

## Final datasheet

### Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology

#### Features

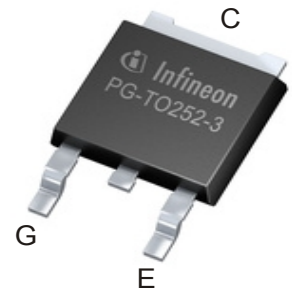
- $V_{CE} = 1200\text{ V}$
- $I_C = 8\text{ A}$
- Low saturation voltage  $V_{CEsat} = 2\text{ V}$  at  $T_{vj} = 150^\circ\text{C}$
- Short circuit ruggedness  $8\ \mu\text{s}$
- Wide range of  $dv/dt$  controllability
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

#### Potential applications

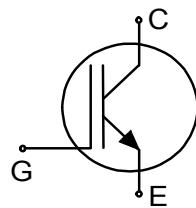
- Industrial drives

#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22
- Encapsulation for the application required



#### Description



Type	Package	Marking
IGD08N120S7	PG-TO252-3	G08MS7

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## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	$L_E$			3		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	reflow soldering (MSL1 according to JEDEC J-STA-020)			260	°C
Thermal resistance, 6 cm <sup>2</sup> Cu on PCB junction to ambient	$R_{th(j-a)}$				50	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.87	1.17	K/W

## 2 IGBT

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25\text{ °C}$	1200	V
DC collector current, limited by $T_{vjmax}$	$I_C$	$T_c = 25\text{ °C}$	24 <sup>1)</sup>	A
		$T_c = 100\text{ °C}$	15	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpulse}$		24	A
Turn-off safe operating area		$V_{CE} \leq 1200\text{ V}, T_{vj} \leq 150\text{ °C}$	24	A
Gate-emitter voltage	$V_{GE}$		±20	V
Transient gate-emitter voltage	$V_{GE}$	$t_p \leq 0.5\ \mu\text{s}, D < 0.001$	±25	V
Short-circuit withstand time	$t_{SC}$	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}$ , Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}, T_{vj} = 150\text{ °C}$	8	μs
Power dissipation	$P_{tot}$	$T_c = 25\text{ °C}$	106	W
		$T_c = 100\text{ °C}$	43	

1) Limited by bondwire

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 8\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.65	2	V
			$T_{vj} = 150\text{ °C}$		2		
Gate-emitter threshold voltage	$V_{GETh}$	$I_C = 0.16\text{ mA}, V_{CE} = V_{GE}$		5.15	5.7	6.45	V
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			20	$\mu\text{A}$
			$T_{vj} = 150\text{ °C}$		130		
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$				100	nA
Transconductance	$g_{fs}$	$I_C = 8\text{ A}, V_{CE} = 20\text{ V}, T_{vj} = 150\text{ °C}$			3.6		S
Short-circuit collector current	$I_{SC}$	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}, t_{SC} \leq 8\text{ }\mu\text{s}$ , Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$ , $T_{vj} = 150\text{ °C}$			38		A
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			1.3		nF
Output capacitance	$C_{oes}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			24		pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			17		pF
Gate charge	$Q_G$	$V_{CC} = 960\text{ V}, I_C = 8\text{ A}, V_{GE} = 15\text{ V}$			55		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		15		ns
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		14		
Rise time (inductive load)	$t_r$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		15		ns
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		18		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		149		ns
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		225		
Fall time (inductive load)	$t_f$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		131		ns
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		246		
Turn-on energy	$E_{on}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		0.46		mJ
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		0.67		
Turn-off energy	$E_{off}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 20\text{ }\Omega, R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 8\text{ A}$		0.41		mJ
			$T_{vj} = 150\text{ °C}, I_C = 8\text{ A}$		0.73		

(table continues...)

**Table 3** (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total switching energy	$E_{ts}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 20\ \Omega,$ $R_{G(off)} = 20\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}, I_C = 8\text{ A}$		0.87	mJ
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 8\text{ A}$		1.4	
Operating junction temperature	$T_{vj}$		-40		150	$^\circ\text{C}$

**Note:** For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

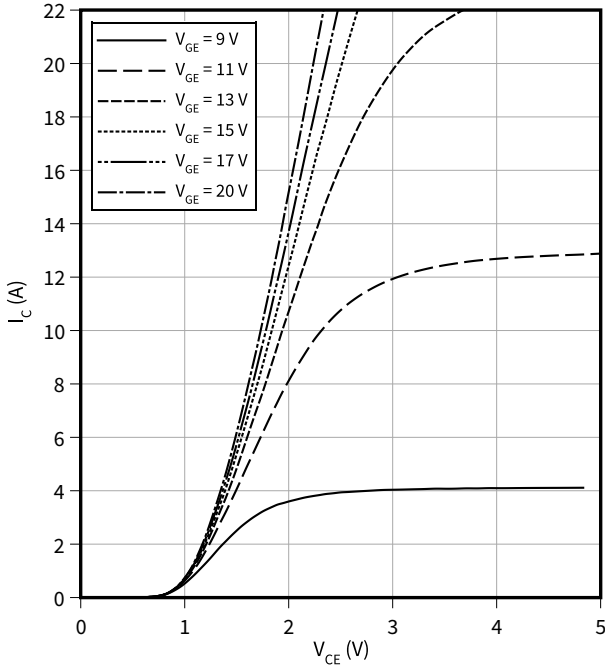
Electrical Characteristic at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified.

Dynamic test circuit, parasitic inductance  $L_\sigma = 45\text{ nH}$ , parasitic capacitor  $C_\sigma = 25\text{ pF}$  from Fig. E. Energy losses include “tail” and diode (IKW08N120CS7) reverse recovery.

### 3 Characteristics diagrams

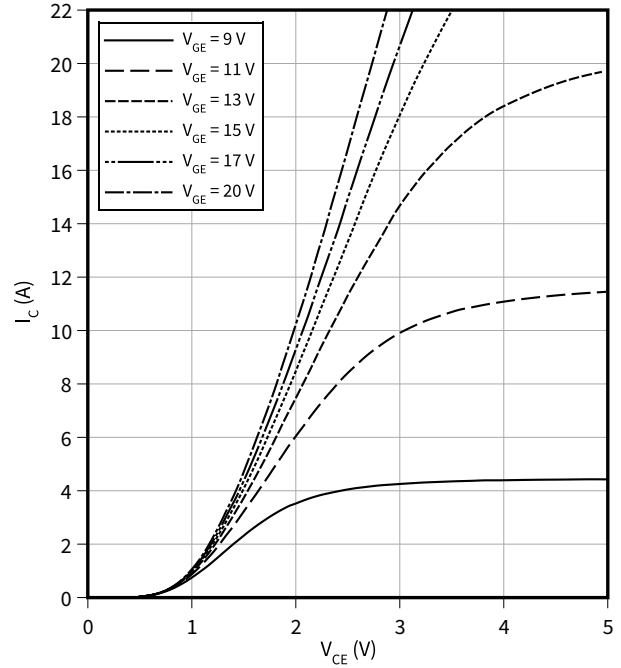
**Typical output characteristic**

$I_C = f(V_{CE})$   
 $T_{vj} = 25\text{ °C}$



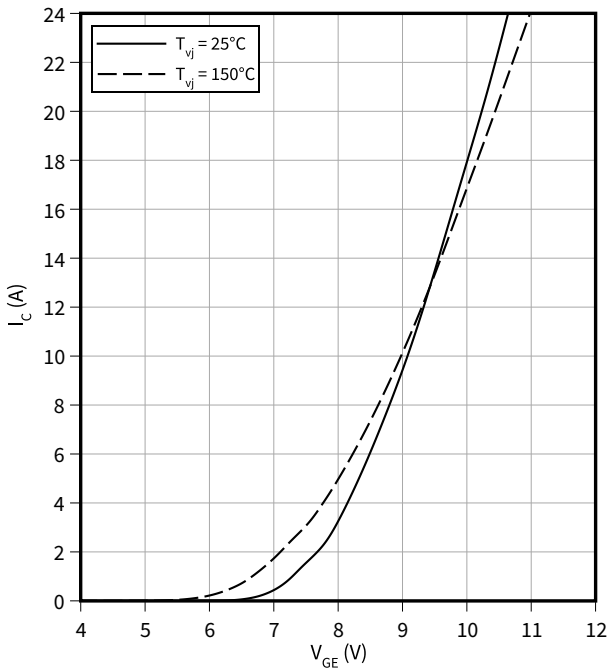
**Typical output characteristic**

$I_C = f(V_{CE})$   
 $T_{vj} = 150\text{ °C}$



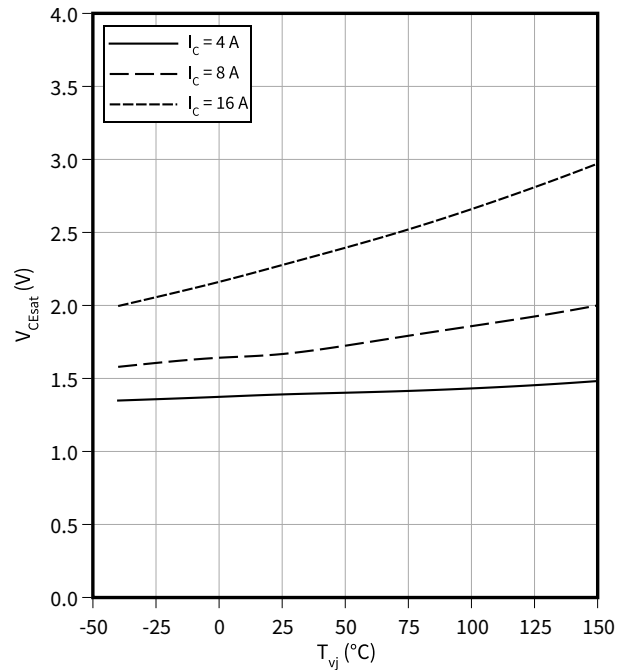
**Typical transfer characteristic**

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



**Typical collector-emitter saturation voltage as a function of junction temperature**

$V_{CEsat} = f(T_{vj})$   
 $V_{GE} = 15\text{ V}$

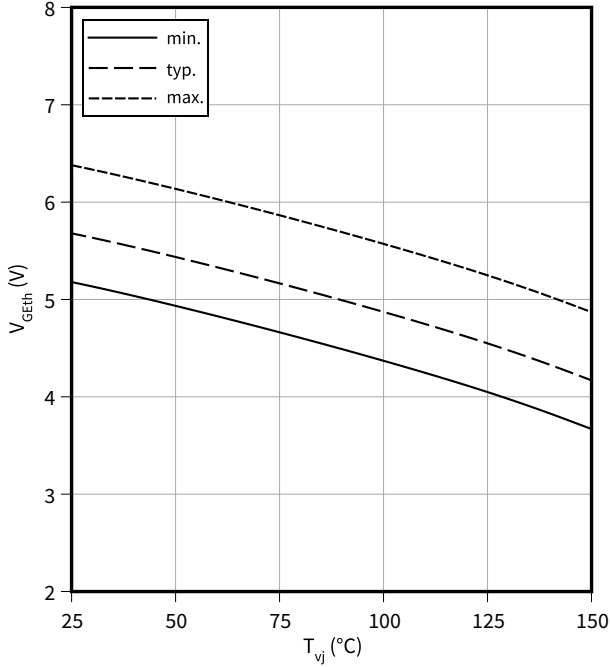


3 Characteristics diagrams

**Gate-emitter threshold voltage as a function of junction temperature**

$V_{GEth} = f(T_{vj})$

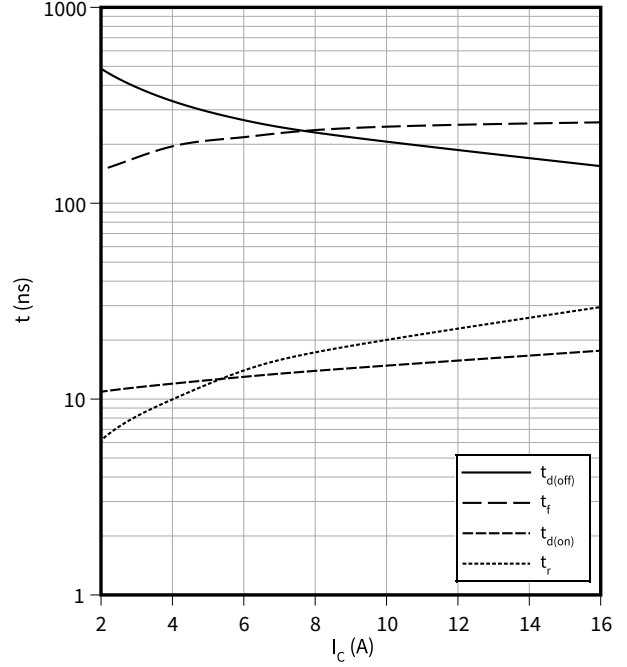
$I_C = 0.16 \text{ mA}$



**Typical switching times as a function of collector current**

$t = f(I_C)$

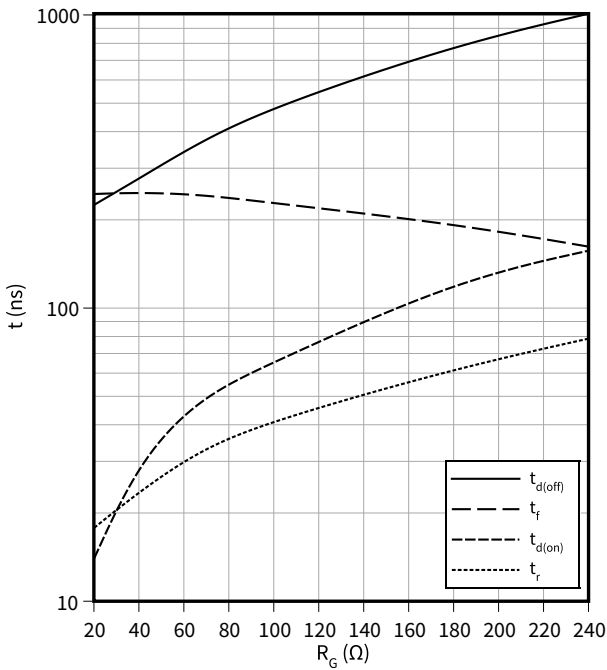
$V_{CC} = 600 \text{ V}, T_{vj} = 150 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 20 \text{ } \Omega$



**Typical switching times as a function of gate resistor**

$t = f(R_G)$

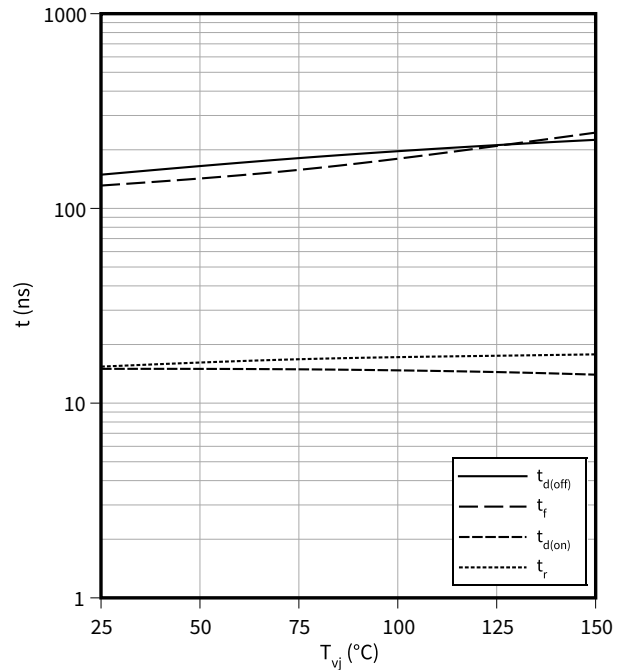
$I_C = 8 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 150 \text{ °C}, V_{GE} = 0/15 \text{ V}$



**Typical switching times as a function of junction temperature**

$t = f(T_{vj})$

$I_C = 8 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 20 \text{ } \Omega$

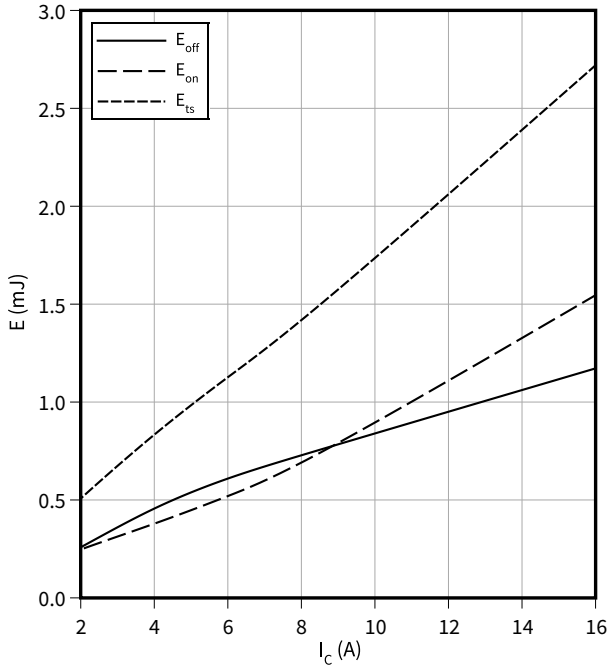


3 Characteristics diagrams

**Typical switching energy losses as a function of collector current**

$E = f(I_C)$

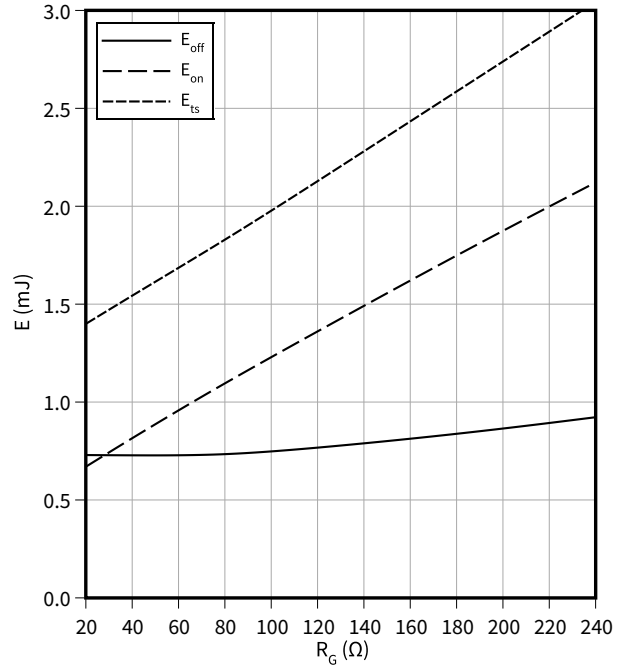
$V_{CC} = 600\text{ V}$ ,  $T_{vj} = 150\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 20\text{ }\Omega$



**Typical switching energy losses as a function of gate resistor**

$E = f(R_G)$

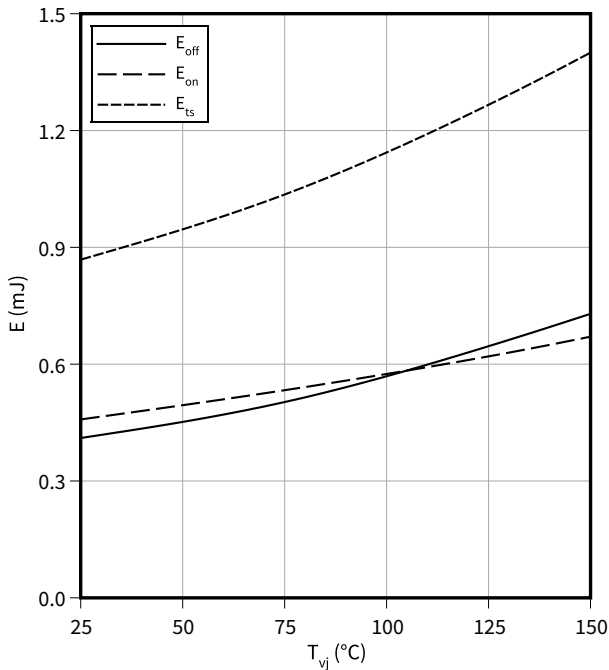
$I_C = 8\text{ A}$ ,  $V_{CC} = 600\text{ V}$ ,  $T_{vj} = 150\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$



**Typical switching energy losses as a function of junction temperature**

$E = f(T_{vj})$

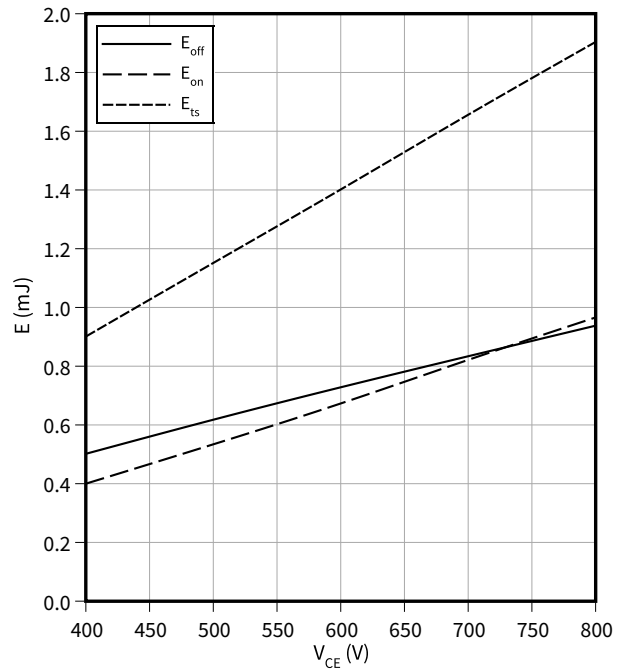
$I_C = 8\text{ A}$ ,  $V_{CC} = 600\text{ V}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 20\text{ }\Omega$



**Typical switching energy losses as a function of collector emitter voltage**

$E = f(V_{CE})$

$I_C = 8\text{ A}$ ,  $T_{vj} = 150\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 20\text{ }\Omega$



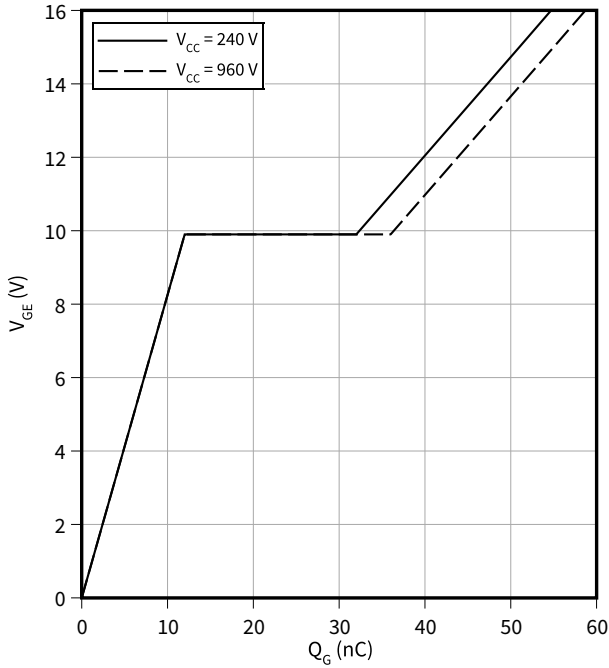


3 Characteristics diagrams

**Typical gate charge**

$V_{GE} = f(Q_G)$

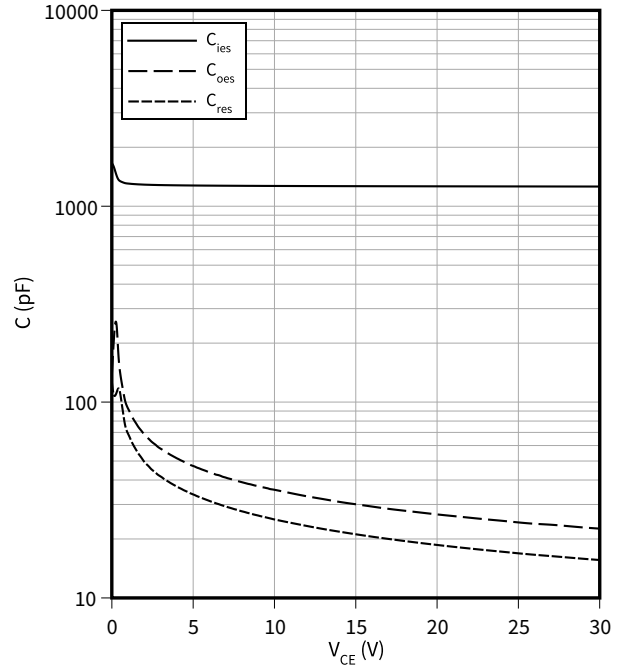
$I_C = 8 \text{ A}$



**Typical capacitance as a function of collector-emitter voltage**

$C = f(V_{CE})$

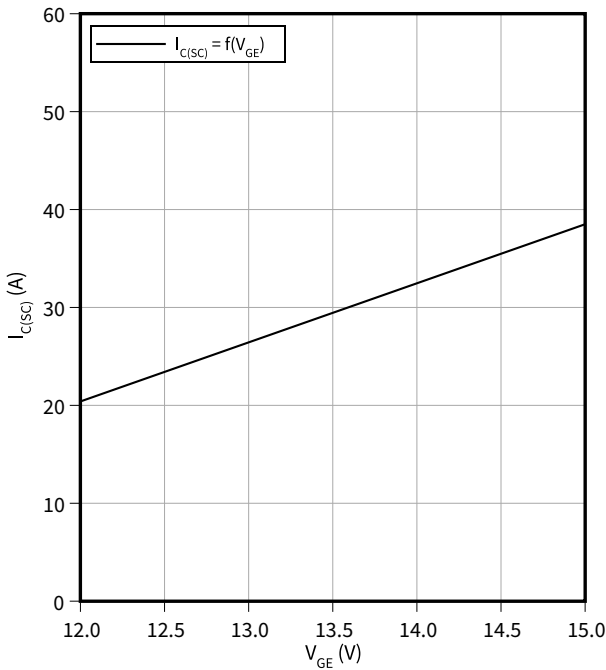
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}$



**Typical short circuit collector current as a function of gate-emitter voltage**

$I_{C(SC)} = f(V_{GE})$

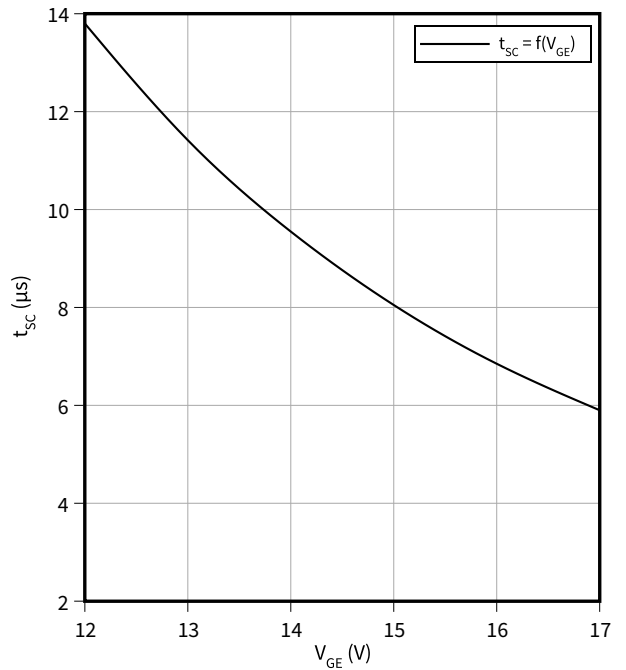
$T_{vj} = 150 \text{ }^\circ\text{C}, V_{CC} = 600 \text{ V}$



**Short circuit withstand time as a function of gate-emitter voltage**

$t_{SC} = f(V_{GE})$

$T_{vj} = 150 \text{ }^\circ\text{C}, V_{CC} = 600 \text{ V}$

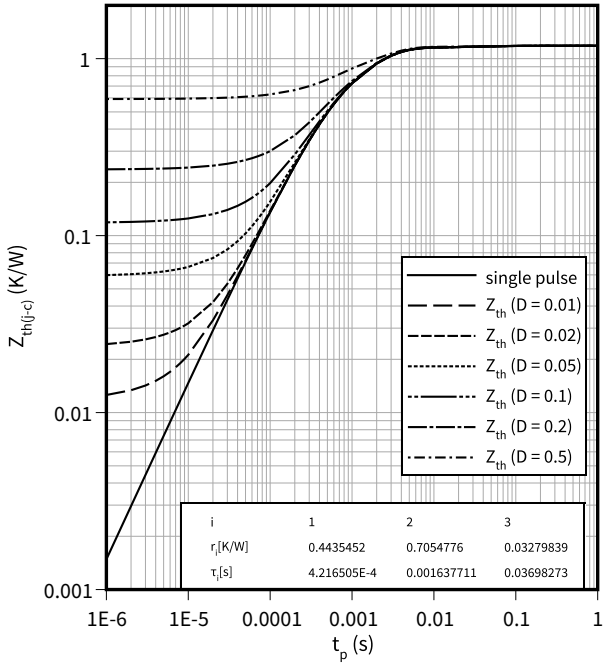


3 Characteristics diagrams

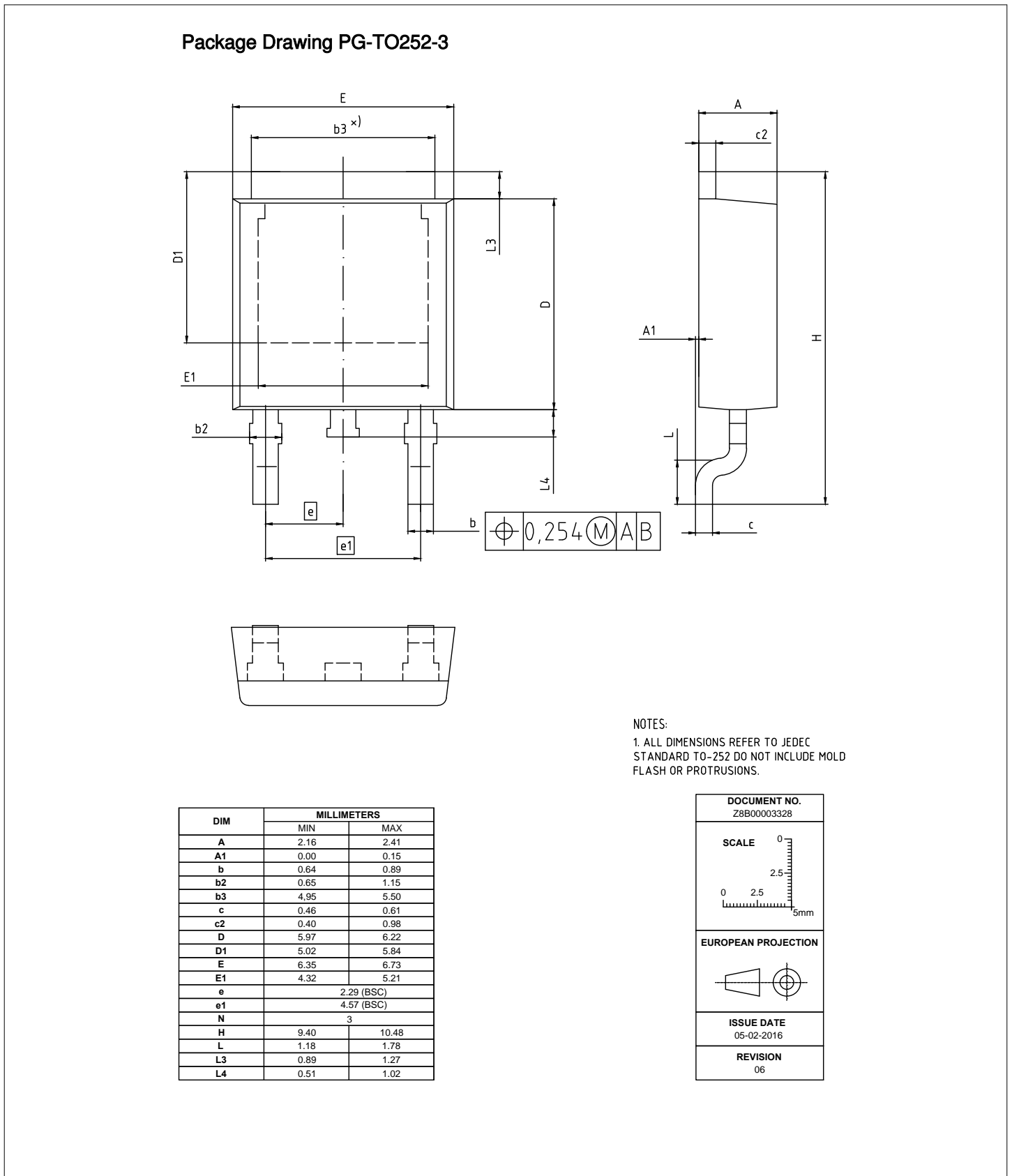
**IGBT transient thermal impedance as a function of pulse width**

$$Z_{th(j-c)} = f(t_p)$$

$$D = t_p/T$$



## 4 Package outlines



**Figure 1**

## 5 Testing conditions

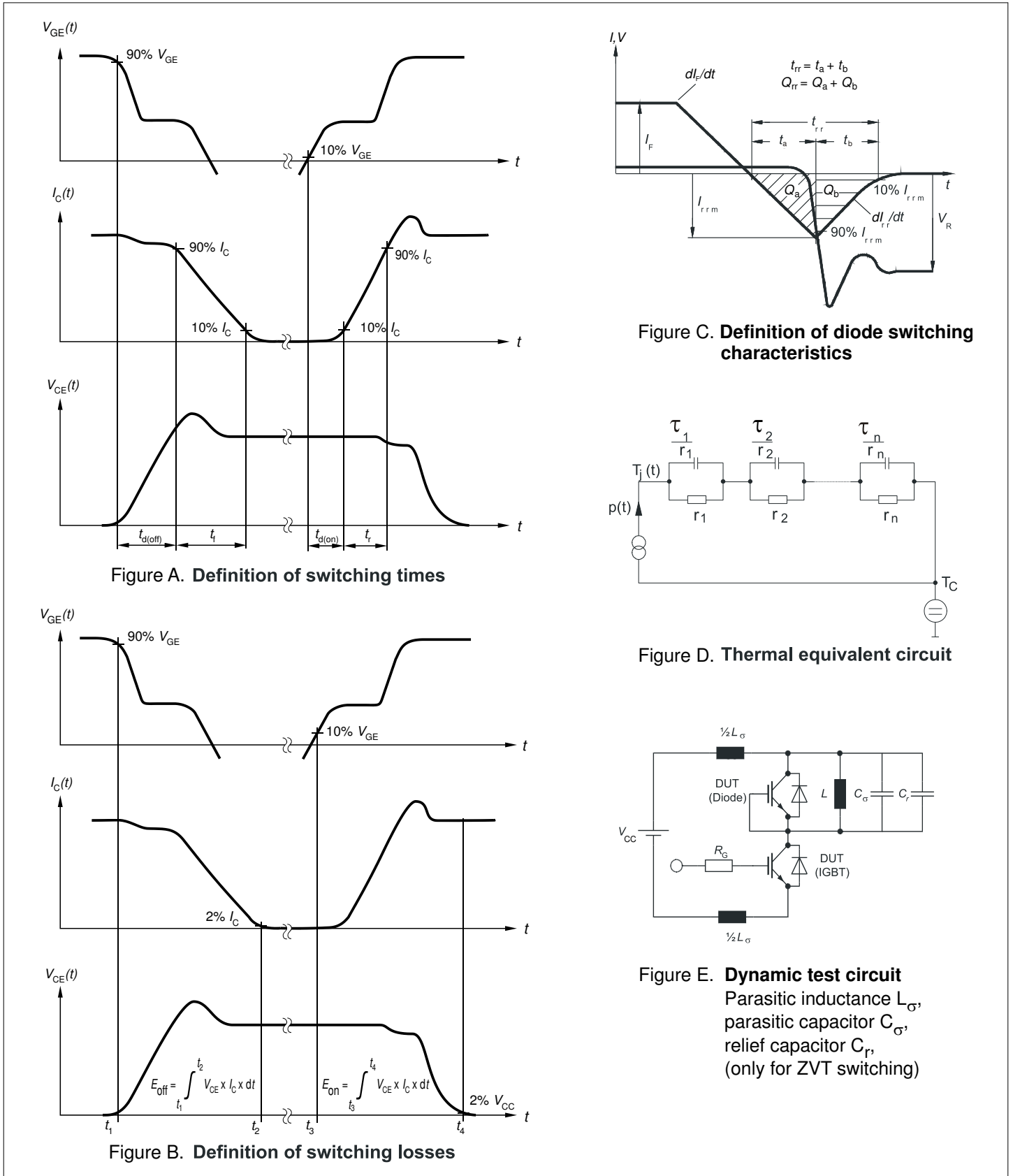


Figure 2

## Revision history

Document revision	Date of release	Description of changes
1.00	2024-03-11	Final datasheet

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